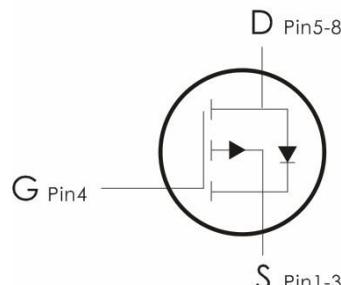
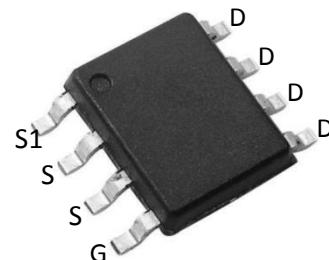


Description:

This P-Channel MOSFET uses advanced trench technology and design to provide excellent $R_{DS(on)}$ with low gate charge. It can be used in a wide variety of applications.



Features:

- 1) $V_{DS}=-40V, I_D=-10A, R_{DS(on)}<15m\Omega @ V_{GS}=-10V$
- 2) Low gate charge.
- 3) Green device available.
- 4) Advanced high cell density trench technology for ultra $R_{DS(on)}$.
- 5) Excellent package for good heat dissipation.

Absolute Maximum Ratings: ($T_C=25^\circ C$ unless otherwise noted)

Symbol	Parameter	Ratings	Units
V_{DS}	Drain-Source Voltage	-40	V
V_{GS}	Gate-Source Voltage	± 20	V
I_D	Continuous Drain Current- $T_C=25^\circ C$	-10	A
	Continuous Drain Current- $T_C=100^\circ C$	-6.3	
	Pulsed Drain Current ¹	-40	
E_{AS}	Single Pulse Avalanche Energy	---	mJ
P_D	Power Dissipation	4.2	W
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to +150	$^\circ C$

Thermal Characteristics:

Symbol	Parameter	Max	Units
$R_{\theta JC}$	Thermal Resistance,Junction to Case	30	$^\circ C/W$
$R_{\theta JA}$	Thermal Resistance,Junction to Ambient	60	

Electrical Characteristics: ($T_C=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
Off Characteristics						
$\mathbf{BV_{DSS}}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250 \mu\text{A}$	-40	---	---	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{GS}=0V, V_{DS}=-40V, T_J=25^\circ\text{C}$	---	---	-1	μA
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0A$	---	---	± 100	nA
On Characteristics						
$V_{GS(th)}$	GATE-Source Threshold Voltage	$V_{GS}=V_{DS}, I_D=250 \mu\text{A}$	-1.0	-1.6	-2.5	V
$R_{DS(ON)}$	Drain-Source On Resistance ²	$V_{GS}=-10V, I_D=-10A$	---	11.5	15	$\text{m}\Omega$
		$V_{GS}=-4.5V, I_D=-8A$	---	16	22	
G_{FS}	Forward Transconductance	$V_{DS}=-10V, I_D=-10A$	---	13	---	S
Dynamic Characteristics						
C_{iss}	Input Capacitance	$V_{DS}=-25V, V_{GS}=0V, f=1\text{MHz}$	---	2757	4000	pF
C_{oss}	Output Capacitance		---	240	360	
C_{rss}	Reverse Transfer Capacitance		---	137	200	
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time ^{2,3}	$V_{DS}=-20V, V_{GS}=-10V$ $I_D=-1A, R_{GEN}=6 \Omega$	---	23	40	ns
t_r	Rise Time ^{2,3}		---	10	20	ns
$t_{d(off)}$	Turn-Off Delay Time ^{2,3}		---	135	250	ns
t_f	Fall Time ^{2,3}		---	46	90	ns
Q_g	Total Gate Charge ^{2,3}	$V_{DS}=-32V, V_{GS}=-4.5V$ $I_D=-1\text{UA}$	---	22.2	40	nC
Q_{gs}	Gate-Source Charge ^{2,3}		---	8.2	16	nC
Q_{gd}	Gate-Drain "Miller" Charge ^{2,3}		---	8.8	16	nC
Drain-Source Diode Characteristics						
V_{SD}	Source-Drain Diode Forward Voltage ²	$V_{GS}=0V, I_S=-1A, T_J=25^\circ\text{C}$	---	---	-1	V

LS	Continuous Source Current	$V_G=V_D=0V$, Force Current	---	-10	A
LSM	Pulsed Source Current		---	-20	A

Notes:

1. Repetitive Rating : Pulsed width limited by maximum junction temperature.
2. The data tested by pulsed , pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.
3. Essentially independent of operating temperature.

Typical Characteristics: ($T_C=25^\circ C$ unless otherwise noted)

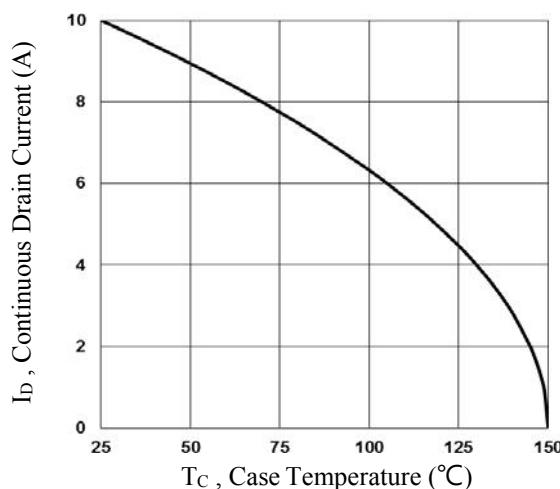


Fig.1 Continuous Drain Current vs. TC

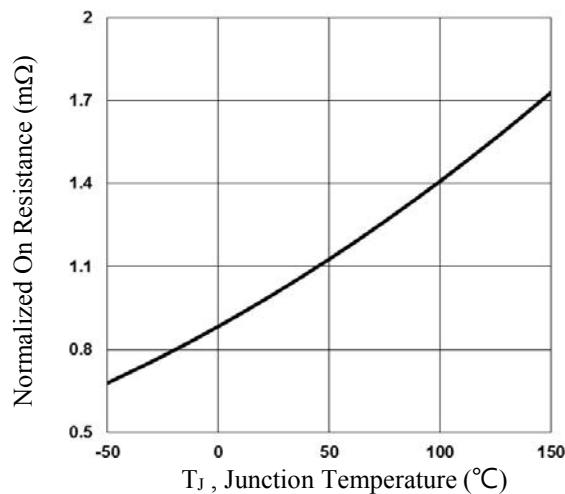


Fig.2 Normalized RDS(on) vs. TJ

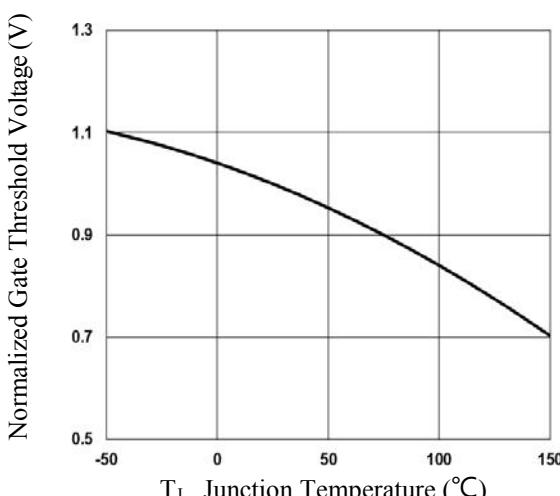


Fig.3 Normalized V_{th} vs. TJ

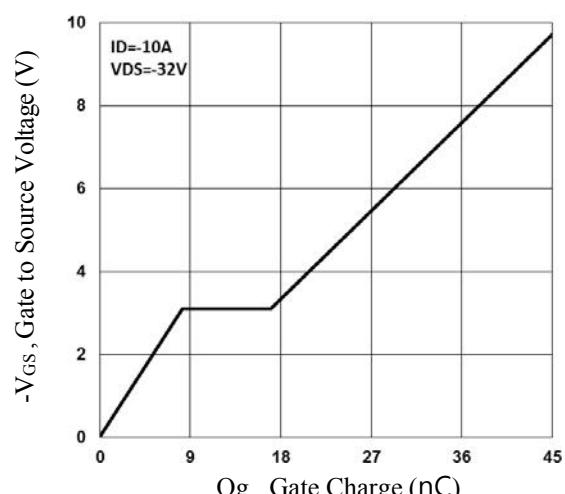


Fig.4 Gate Charge Waveform

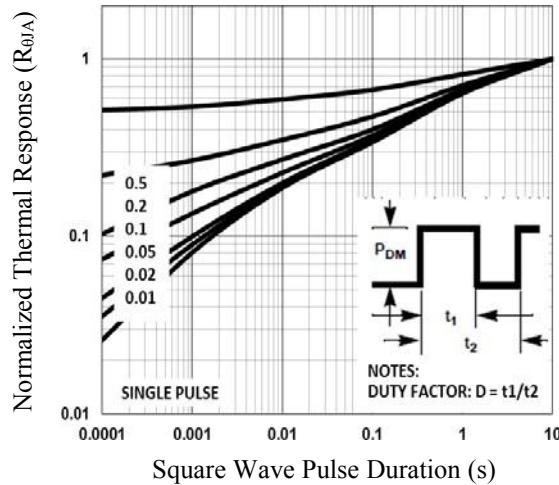


Fig.5 Normalized Transient Impedance

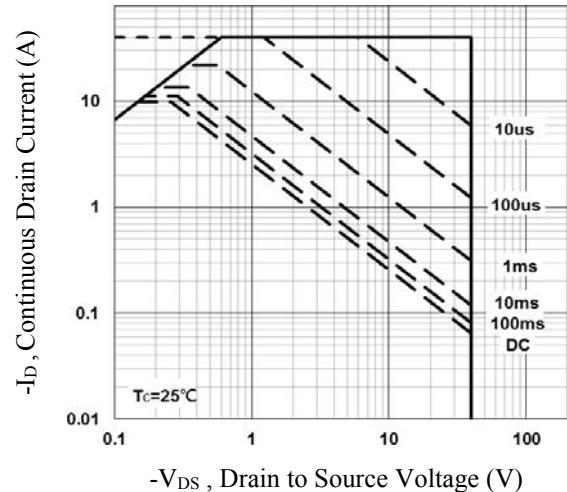


Fig.6 Maximum Safe Operation Area

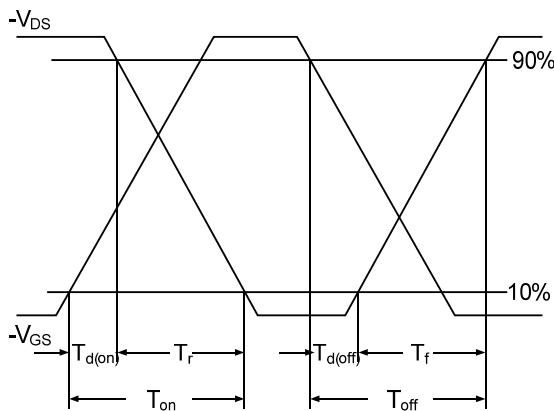


Fig.7 Switching Time Waveform

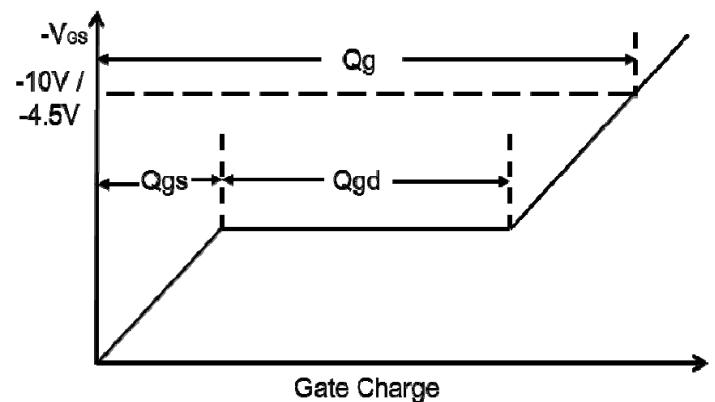
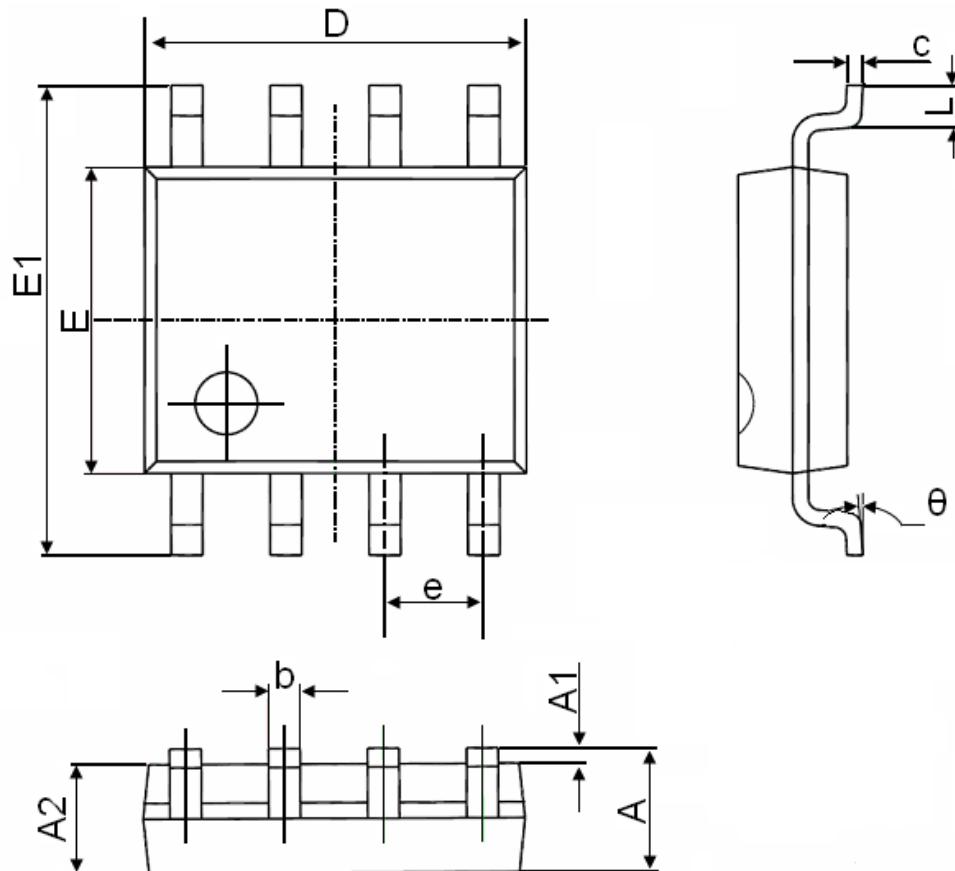


Fig.8 Gate Charge Waveform

SOP-8 Package Information

Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.006	0.010
D	4.700	5.100	0.185	0.200
E	3.800	4.000	0.150	0.157
E1	5.800	6.200	0.228	0.244
e	1.270(BSC)		0.050(BSC)	
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°